

Silicon Epitaxial Planar Transistor

2SA1179

FEATURES

- High breakdown voltage.

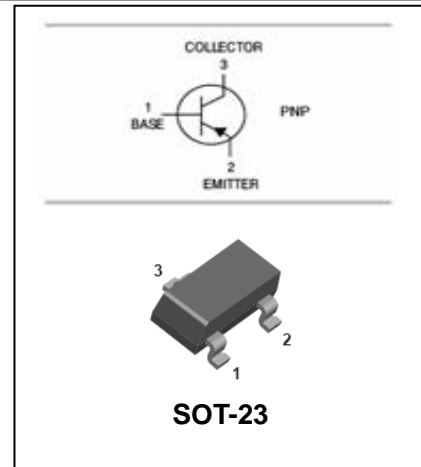


Lead-free

APPLICATIONS

- General purpose application.

ORDERING INFORMATION



Type No.	Marking	Package Code
2SA1179	M	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-55	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	°C

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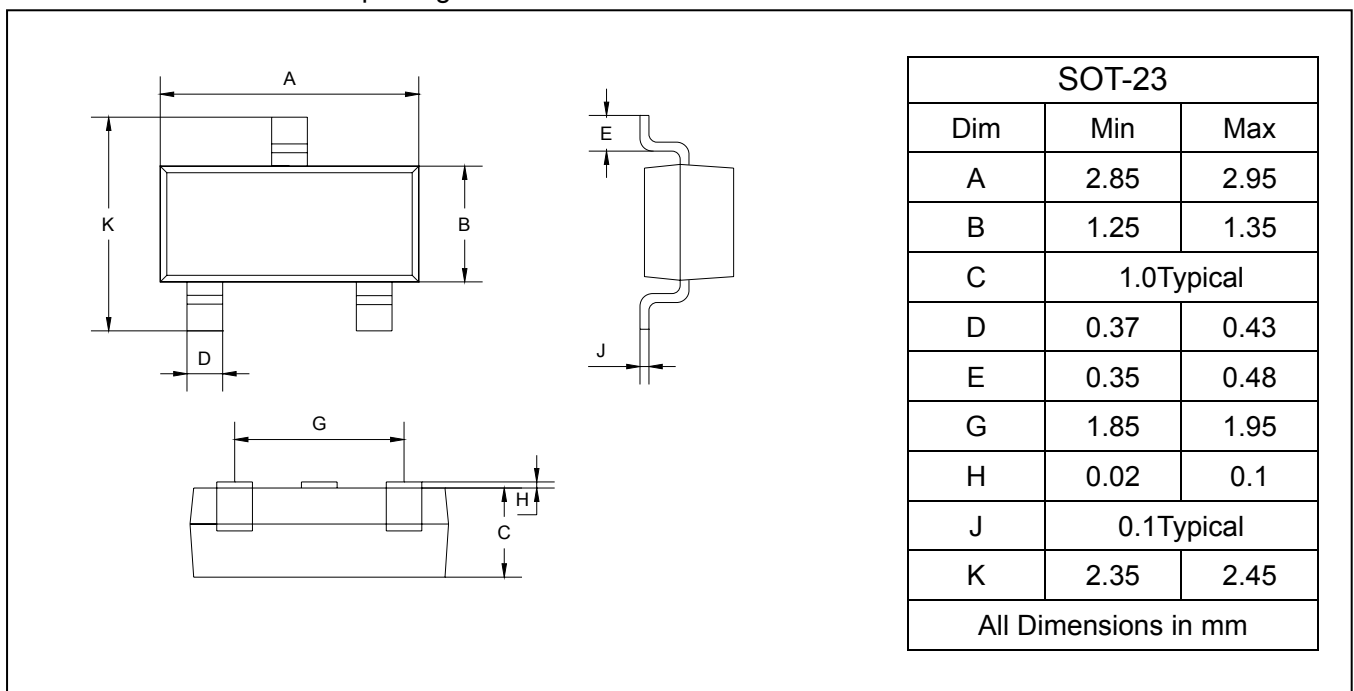
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-1mA$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50mA, I_B=-5mA$			-1.0	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-10mA$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6V, I_E=0, f=1MHz$		4		pF

PACKAGE OUTLINE

Plastic surface mounted package

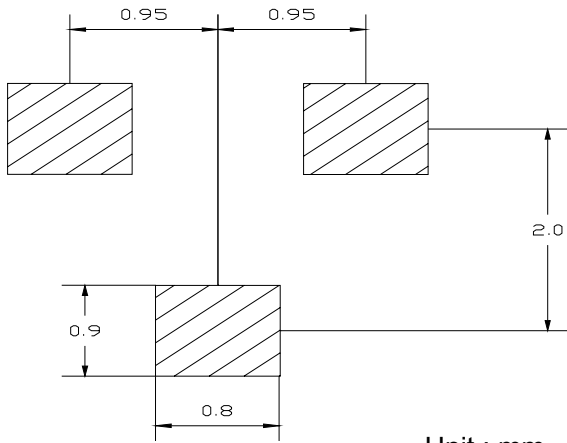
SOT-23



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SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA1179	SOT-23	3000/Tape&Reel